

# **NCE N-Channel Super Trench II Power MOSFET**

## **Description**

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

## **Application**

- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

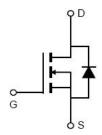
#### **General Features**

- $V_{DS}$  =100V, $I_D$  =75A  $R_{DS(ON)}$ =7.4m $\Omega$ , typical (TO-220)@  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

**TO-220** 





**Schematic Diagram** 

## **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP080N10	NCEP080N10	TO-220	-	-	-

## Absolute Maximum Ratings (T<sub>c</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	78	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100°C)	55	А
Pulsed Drain Current	I <sub>DM</sub>	300	Α
Maximum Power Dissipation	P <sub>D</sub>	120	W
Derating factor		0.8	W/℃
Single pulse avalanche energy (Note 4)	E <sub>AS</sub>	420	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	°C

### **Thermal Characteristic**

Thermal Resistance,Junction-to-Case	R <sub>eJC</sub>	1.25	°C/W
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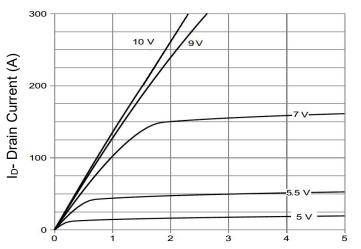
# Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},\ I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =37.5A	-	7.4	8.0	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =37.5A		60	-	S
Dynamic Characteristics (Note3)						
Input Capacitance	C <sub>lss</sub>		-	3070	-	pF
Output Capacitance	Coss	V <sub>DS</sub> =50V,V <sub>GS</sub> =0V, F=1.0MHz	-	290	-	pF
Reverse Transfer Capacitance	Crss	F-1.UIVIHZ	-	23	-	pF
Switching Characteristics (Note 3)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	15	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =50 $V$ , $I_{D}$ =37.5 $A$	-	10	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{G}$ =1.6 $\Omega$	-	34	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS
Total Gate Charge	Qg	V _F0V/L _27.FA	-	53	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =50V,I <sub>D</sub> =37.5A,	-	18	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	16	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 2)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =37.5A	-	-	1.2	V
Diode Forward Current	Is		-	-	75	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C, I_F = 37.5A$	-	60	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	106	-	nC

### Notes:

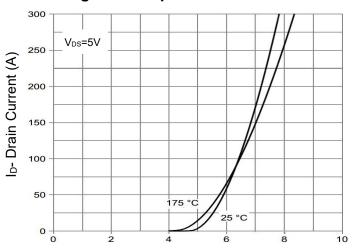
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3. Guaranteed by design, not subject to production
- 4. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=50V,V\_G=10V,L=0.25mH,Rg=25 $\Omega$

# **Typical Electrical and Thermal Characteristics**



Vds Drain-Source Voltage (V)





Vgs Gate-Source Voltage (V)
Figure 2 Transfer Characteristics

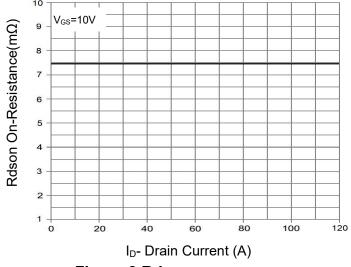
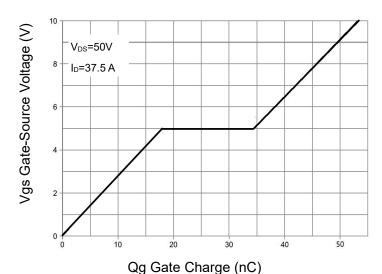


Figure 3 Rdson- Drain Current



**Figure 4 Gate Charge** 

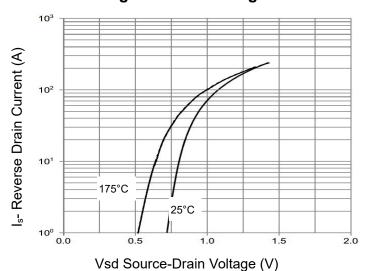


Figure 5 Source- Drain Diode Forward

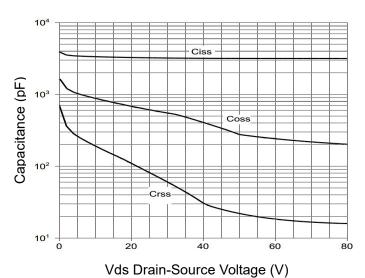
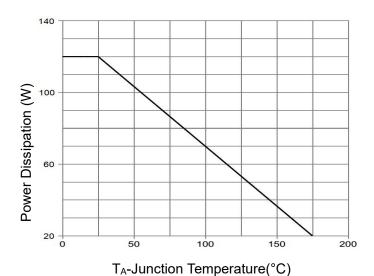


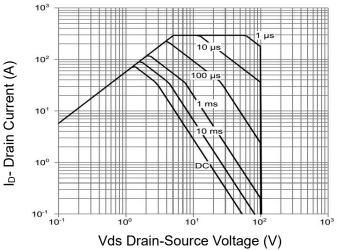
Figure 6 Capacitance vs Vds

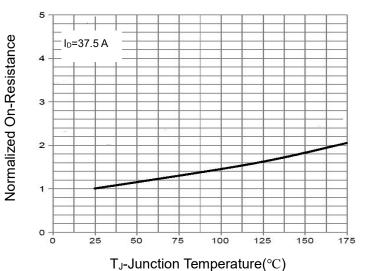


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Figure 7 Power De-rating

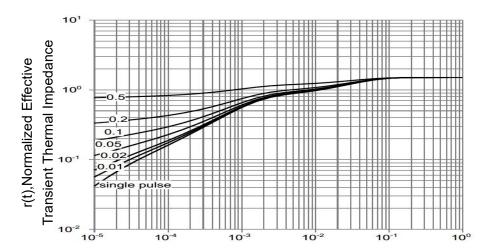
T<sub>A</sub>-Junction Temperature (°C) **Figure 9 Current De-rating** 





**Figure 8 Safe Operation Area** 

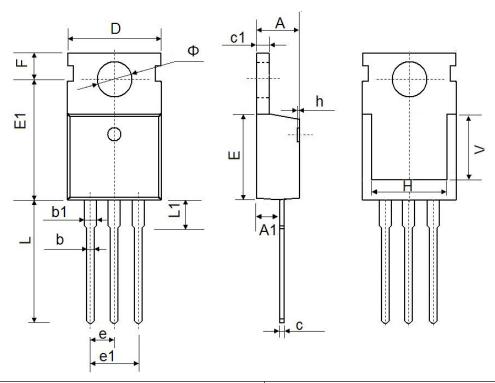
Figure 10 Rdson-Junction Temperature



Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

# **TO-220-3L Package Information**



Comple of	Dimensions	In Millimeters	Dimensions In Inches				
Symbol	Min.	Max.	Min.	Max.			
Α	4.400	4.600	0.173	0.181			
A1	2.250	2.550	0.089	0.100			
b	0.710	0.910	0.028	0.036			
b1	1.170	1.370	0.046	0.054			
С	0.330	0.650	0.013	0.026			
c1	1.200	1.400	0.047	0.055			
D	9.910	10.250	0.390	0.404			
E	8.9500	9.750	0.352	0.384			
E1	12.650	12.950	0.498	0.510			
е	2.540	2.540 TYP.		0.100 TYP.			
e1	4.980	5.180	0.196	0.204			
F	2.650	2.950	0.104	0.116			
Н	7.900	8.100	0.311	0.319			
h	0.000	0.300	0.000	0.012			
L	12.900	13.400	0.508	0.528			
L1	2.850	3.250	0.112	0.128			
V	6.900 REF.		0.276 REF.				
Ф	3.400	3.800	0.134	0.150			

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